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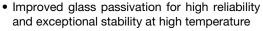
Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 16 A



| PRIMARY CHARACTERISTICS | | | | | |
|------------------------------------|--|--|--|--|--|
| I _{T(AV)} | 16 A | | | | |
| V _{DRM} /V _{RRM} | 100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V | | | | |
| V _{TM} | 1.75 V | | | | |
| I _{GT} | 60 mA | | | | |
| T _J | -65 °C to +125 °C | | | | |
| Package | TO-48 (TO-208AA) | | | | |
| Circuit configuration | Single SCR | | | | |

FEATURES





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- · Phase control applications

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|------------------------------------|-----------------|-------------|------------------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | |
| 1 | | 16 | А | | |
| I _{T(AV)} | T _C | 85 | °C | | |
| I _{T(RMS)} | | 35 | A | | |
| I _{TSM} | 50 Hz | 340 | ^ | | |
| | 60 Hz | 360 | A A | | |
| l ² t | 50 Hz | 574 | 120 | | |
| | 60 Hz | 524 | A ² s | | |
| V _{DRM} /V _{RRM} | | 100 to 1200 | V | | |
| tq | Typical | 110 | μs | | |
| TJ | | -65 to +125 | °C | | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | | | |
|-----------------|-----------------|---|---|--|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V | $\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} &= T_{J} & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$ | | | |
| | 10 | 100 | 150 | 20 | | | |
| | 20 | 200 | 300 | | | | |
| 4 | 40 | 400 | 500 | | | | |
| VS-16RIA | 60 | 600 | 700 | 10 | | | |
| | 80 | 800 | 900 | 10 | | | |
| | 100 | 1000 | 1100 | | | | |
| | 120 | 1200 | 1300 | | | | |

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $[\]ensuremath{^{(2)}}$ For voltage pulses with $t_p \leq 5 \ ms$



| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|---|---------------------|---|--|--|--------|------------------|
| PARAMETER | SYMBOL | | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average on-state current | | 100° oinuooi | dal conduction | | 16 | Α |
| at case temperature | I _{T(AV)} | 100 Siliusoi | idal conduction | | 85 | °C |
| Maximum RMS on-state current | I _{T(RMS)} | | | | 35 | Α |
| | | t = 10 ms | No voltage | | 340 | |
| Maximum peak, one-cycle | | t = 8.3 ms | reapplied | | 360 | ^ |
| non-repetitive surge current | I _{TSM} | t = 10 ms | 100 % V _{RRM} | - | 285 | Α |
| | | t = 8.3 ms | reapplied | Sinusoidal half wave, | 300 | |
| Maximum I ² t for fusing | | t = 10 ms | No voltage | No voltage reapplied initial $T_J = T_J$ maximum 100 % V_{RRM} | 574 | A ² s |
| | | t = 8.3 ms | reapplied | | 524 | |
| | l ² t | t = 10 ms | 100 % V _{RRM} reapplied | | 405 | |
| | | t = 8.3 ms | | | 375 | |
| Maximum I ² √t for fusing | I²√t | t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum | | 5740 | A²√s | |
| Low level value of threshold voltage | V _{T(TO)1} | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $I_{J} = I_{J}$ maximum | | 0.97 | V | |
| High level value of threshold voltage | V _{T(TO)2} | $(I > \pi \times I_{T(AV)})$ | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ | | 1.24 | |
| Low level value of on-state slope resistance | r _{t1} | (16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $I_{J} = I_{J}$ maximum | | 17.9 | mΩ | |
| High level value of on-state slope resistance | r _{t2} | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ | | 13.6 | 11122 | |
| Maximum on-state voltage | V_{TM} | I _{pk} = 50 A, T _J = 25 °C | | 1.75 | V | |
| Maximum holding current | I _H | T 05.00 a | T _J = 25 °C, anode supply 6 V, resistive load | | 130 | A |
| Latching current | ΙL | $I_{\rm J} = 25 {}^{\circ}{\rm C}, 8$ | | | 200 | - mA |

| SWITCHING | | | | | |
|-------------------------------|--------------------------|-------------------|--|-----|--------|
| PARAMETER | | SYMBOL | SYMBOL TEST CONDITIONS | | UNITS |
| | $V_{DRM} \leq 600 \ V$ | | | 200 | |
| Maximum rate of rise | $V_{DRM} \leq 800 \ V$ | 41/4 + | dI/dt | 180 | - A/μs |
| of turned-on current - | $V_{DRM} \leq 1000 \; V$ | ui/ut | | 160 | |
| | $V_{DRM} \leq 1600 \; V$ | | | 150 | |
| Typical turn-on time | | t _{gt} | T_J = 25 °C, at rated V_{DRM}/V_{RRM} , T_J = 125 °C | 0.9 | |
| Typical reverse recovery time | | t _{rr} | $T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \mu s$, $dI/dt = -10 A/\mu s$ | 4 | μs |
| Typical turn-off time | | t _q | $T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W | 110 | |

Note

• t_q = 10 μs up to 600 V, t_q = 30 μs up to 1600 V available on special request

| BLOCKING | | | | |
|-------------------------------|--------|--|---------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise | dV/dt | T _J = T _J maximum linear to 100 % rated V _{DRM} | 100 | V/µs |
| of off-state voltage | uv/ut | T _J = T _J maximum linear to 67 % rated V _{DRM} | 300 (1) | v/μS |

Note

 $^{^{(1)}}$ Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 16RIA120S90



| TRIGGERING | | | | | |
|-------------------------------------|--------------------|---|---|--------|-------|
| PARAMETER | SYMBOL | TES | T CONDITIONS | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | $T_{.1} = T_{.1}$ maximum | | 8.0 | W |
| Maximum average gate power | P _{G(AV)} | ıj = ıj maximum | | 2.0 | VV |
| Maximum peak positive gate current | I _{GM} | $T_J = T_J$ maximum | | 1.5 | Α |
| Maximum peak negative gate voltage | -V _{GM} | T _J = T _J maximum | | 10 | V |
| | | T _J = - 65 °C | | 90 | |
| DC gate current required to trigger | I _{GT} | T _J = 25 °C | Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied | 60 | mA |
| | | T _J = 125 °C | | 35 | |
| | V _{GT} | T _J = - 65 °C | | 3.0 | |
| DC gate voltage required to trigger | | T _J = 25 °C | | 2.0 | V |
| | | T _J = 125 °C | | 1.0 | |
| DC gate current not to trigger | I _{GD} | T _J = T _J maximum, V _{DRM} = Rated value | | 2.0 | mA |
| DC gate voltage not to trigger | V _{GD} | $T_J = T_J$ maximum, $V_{DRM} = Rated value$ | Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied | 0.2 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|---|--------------------|-----------|----------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | | UNITS | |
| Maximum operating junction and storage temperature range | T _J , T _{Stg} | | -65 to +125 | | °C | |
| Maximum thermal resistance, junction to case | R _{thJC} | DC operation | 0. | 86 | K/W | |
| Maximum thermal resistance, case to heat sink | R _{thCS} | Mounting surface, smooth, flat and greased 0.35 | | 35 | 1 10 00 | |
| | | | TO NUT | TO DEVICE | | |
| | | | 20 (27.5) | 25 | lbf ⋅ in | |
| Mounting torque | | Lubricated threads (Non-lubricated threads) | 0.23 (0.32) | 0.29 | kgf · m | |
| | | (ton labilitation amount) | 2.3 (3.1) | 2.8 | N·m | |
| Approximate weight | | | 1 | 4 | g | |
| Approximate weight | | | 0. | 49 | oz. | |
| Case style | | See dimensions - link at the end of datasheet | t TO-48 (TO-208AA) | |) | |

| △R _{thJC} CONDUCTION | | | | |
|-------------------------------|-----------------------|------------------------|---------------------|-------|
| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS | UNITS |
| 180° | 0.21 | 0.15 | | |
| 120° | 0.25 | 0.25 | | |
| 90° | 0.31 | 0.34 | $T_J = T_J$ maximum | K/W |
| 60° | 0.45 | 0.47 | | |
| 30° | 0.76 | 0.76 | | |

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

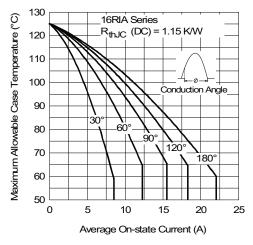


Fig. 1 - Current Ratings Characteristics

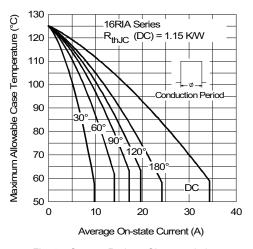


Fig. 2 - Current Ratings Characteristics

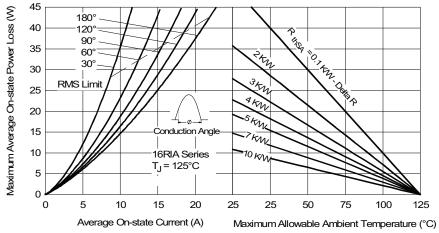


Fig. 3 - On-State Power Loss Characteristics

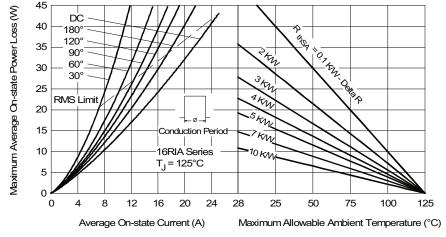


Fig. 4 - On-State Power Loss Characteristics

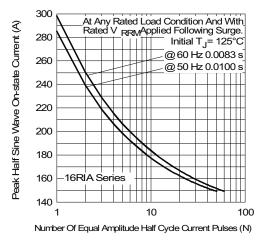


Fig. 5 - Maximum Non-Repetitive Surge Current

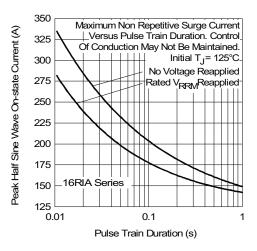


Fig. 6 - Maximum Non-Repetitive Surge Current

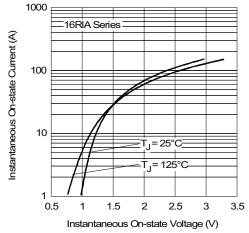


Fig. 7 - Forward Voltage Drop Characteristics

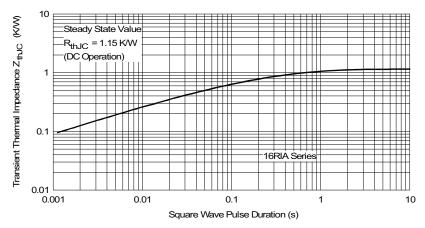


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



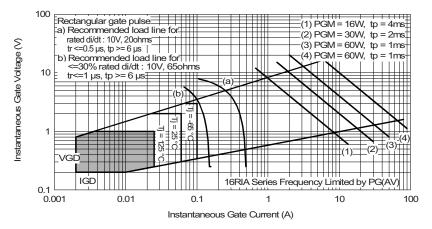
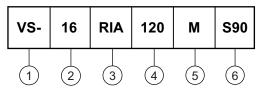


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

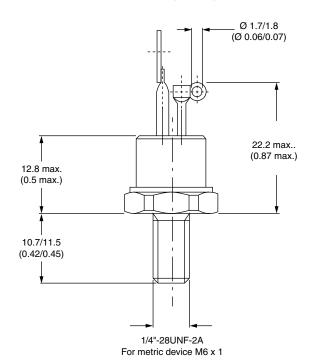
S90 = 1000 V/µs (special selection)

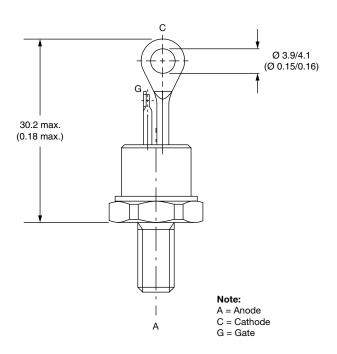
| LINKS TO RELATED DOCUMENTS | | | |
|----------------------------|--------------------------|--|--|
| Dimensions | www.vishay.com/doc?95333 | | |

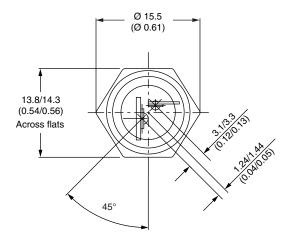


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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